

BC350 TRANSISTOR (PNP)**FEATURES**

Power dissipation

 P_{CM} : 0.3 W (Tamb=25°C)

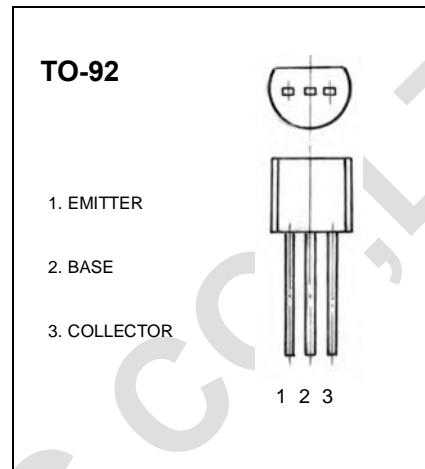
Collector current

 I_{CM} : -0.1 A

Collector-base voltage

 $V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

 T_J, T_{stg} : -55°C to +150°C**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -35V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -2mA$	40		450	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -10mA, I_B = -1mA$			-0.3	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = -10mA, I_B = -1mA$			-1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA, f = 30MHz$	125			MHz